Fearch Hort. ff. (15 pp.) (7/26/04)

		di d	· • • • • • • • • • • • • • • • • • • •	(, , , , , , , , , , , , , , , , , , ,
L Number	Hits	Search Text	DB	Time stamp
1	7941	((257/68) or (257/71) or (257/277) or	USPAT;	2004/07/26 11:15
		(257/296) or (257/298) or (257/300) or	US-PGPUB;	
		(257/303) or (257/306) or (257/516) or	EPO; JPO;	
		(257/701) or (257/700)).CCLS.	DERWENT;	
			IBM_TDB	
2	1191	257/309	USPAT;	2004/07/26 11:16
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	2220	257/206	IBM TDB	2004/07/26 11:16
3	3238	257/306	USPAT;	2004/07/26 11:16
			US-PGPUB; EPO; JPO;	
ĺ			DERWENT;	
			IBM TDB	
4	2276	257/532	USPAT;	2004/07/26 11:16
1	22,0	2377 332	US-PGPUB;	2001/01/20 11:10
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
5	427	257/534	USPAT;	2004/07/26 11:16
			US-PGPUB;	
		·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	11391	(((257/68) or (257/71) or (257/277) or	USPAT;	2004/07/26 11:16
		(257/296) or (257/298) or (257/300) or	US-PGPUB;	
		(257/303) or (257/306) or (257/516) or	EPO; JPO;	
		(257/701) or (257/700)).CCLS.) 257/309	DERWENT;	
	_	257/306 257/532 257/534	IBM_TDB	0004/07/06 11 10
7	5		USPAT;	2004/07/26 11:18
		(257/296) or (257/298) or (257/300) or	US-PGPUB;	
		(257/303) or (257/306) or (257/516) or (257/701) or (257/700)).CCLS.) 257/309	EPO; JPO; DERWENT;	
		257/306 257/532 257/534) and (BPSG	IBM TDB	
		boro-phospho adj silicate adj glass) near3	1514-155	
		(germanium ge) and etch\$3 and (corrugat\$3		
		rippl\$3 rougness rough)		
8	3	(((257/68) or (257/71) or (257/277) or	USPAT;	2004/07/26 11:18
		(257/296) or (257/298) or (257/300) or	US-PGPUB;	
		(257/303) or (257/306) or (257/516) or	EPO; JPO;	
		(257/701) or (257/700)).CCLS.) and (BPSG	DERWENT;	
		boro-phospho adj silicate adj glass) near3	IBM_TDB	
		(germanium ge) and etch\$3 and (corrugat\$3		
		rippl\$3 rougness rough)		
-	77	(boro-silicate adj glass or bpsg or	USPAT;	2004/07/23 16:33
		germanium adj boro-silicate glass or	US-PGPUB;	
		ge-bpsg) and capacitor and dram and	EPO; JPO;	
		(corrugat\$3 or rippl\$3)	DERWENT;	
_	0	((boro-silicate adj glass or bpsg or	IBM_TDB USPAT;	2002/02/08 14:00
-	ا	germanium adj boro-silicate glass or	US-PGPUB;	2002/02/00 14:00
	!	ge-bpsg) and capacitor and dram and	EPO; JPO;	
		(corrugat\$3 or rippl\$3)) and (rippl\$3 or	DERWENT;	
		corrugat\$3) near12 (capacitor adj2 wall)	IBM TDB	
-	3	((boro-silicate adj glass or bpsg or	USPAT;	2002/02/08 14:00
]		germanium adj boro-silicate glass or	US-PGPUB;	
		ge-bpsg) and capacitor and dram and	EPO; JPO;	
		(corrugat\$3 or rippl\$3)) and (rippl\$3 or	DERWENT;	
		corrugat\$3) near12 (capacitor adj2 (plate	IBM_TDB	
		or wall))	-	
-	43	(((borosilicate or boro-silicate) adj	USPAT;	2002/02/08 14:14
		glass or bpsg or germanium adj	US-PGPUB;	
j		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
		or ge-bpsg) near12 (stack\$2 or	DERWENT;	
		alternat\$3)) same capacitor and (memory	IBM_TDB	
		adj3 (cell or device)) and dram		

		_		
_	43	((((borosilicate or boro-silicate) adj glass or bpsg or germanium adj	USPAT; US-PGPUB;	2002/02/08 14:14
		(borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (stack\$2 or	EPO; JPO; DERWENT;	
		alternat\$3)) same capacitor) and (memory	IBM_TDB	
-	0	adj3 (cell or device)) and dram ((((borosilicate or boro-silicate) adj	USPAT;	2002/02/08 14:15
		glass or bpsg or germanium adj	US-PGPUB;	
		(borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (stack\$2 or	EPO; JPO; DERWENT;	
	}	alternat\$3)) same (rippl\$3 or corrugat\$3) same capacitor) and (memory adj3 (cell or	IBM_TDB	
		device)) and dram		:
-	41	((((borosilicate or boro-silicate) adj glass or bpsg or germanium adj	USPAT; US-PGPUB;	2002/02/08 14:16
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
		or ge-bpsg) near12 (stack\$2 or alternat\$3)) same capacitor) and (rippl\$3	DERWENT; IBM TDB	
		or stack\$2) and (memory adj3 (cell or	_	
_	2	device)) and dram ((((borosilicate or boro-silicate) adj	USPAT;	2002/02/08 14:19
		glass or bpsg or germanium adj (borosilicate or boro-silicate) adj glass	US-PGPUB; EPO; JPO;	
		or ge-bpsg) near12 (stack\$2 or	DERWENT;	
		alternat\$3)) same capacitor) and ((rippl\$3 or stack\$2) near12 (capacitor adj2 (plate	IBM_TDB	
		or wall))) and (memory adj3 (cell or		
_	0	<pre>device)) and dram ((((borosilicate or boro-silicate) adj</pre>	USPAT;	2002/02/08 14:20
		glass or bpsg or germanium adj	US-PGPUB;	
		(borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (stack\$2 or	EPO; JPO; DERWENT;	
		alternat\$3)) same capacitor) and ((rippl\$3 or corrugat\$2) near12 (capacitor adj2	IBM_TDB	
		(plate or wall))) and (memory adj3 (cell		
_	0	or device)) and dram ((((borosilicate or boro-silicate) adj	USPAT;	2002/02/08 14:20
		glass or bpsg or germanium adj (borosilicate or boro-silicate) adj glass	US-PGPUB; EPO; JPO;	
		or ge-bpsg) near12 (stack\$2 or	DERWENT;	
		alternat\$3)) same capacitor) and ((rippl\$3 or corrugat\$2) near12 (plate or wall)) and	IBM_TDB	
		(memory adj3 (cell or device)) and dram	IIODAM -	2002/02/00 14:21
_	0	((((borosilicate or boro-silicate) adj glass or bpsg or germanium adj	USPAT; US-PGPUB;	2002/02/08 14:21
		<pre>(borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (stack\$2 or</pre>	EPO; JPO; DERWENT;	
		alternat\$3)) same capacitor) and ((rippl\$3	IBM_TDB	
		or corrugat\$2) near12 (plate or wall)) and dram		
-	0	((((borosilicate or boro-silicate) adj	USPAT;	2002/02/08 14:21
		glass or bpsg or germanium adj (borosilicate or boro-silicate) adj glass	US-PGPUB; EPO; JPO;	
	!	or ge-bpsg) near12 (stack\$2 or alternat\$3)) same capacitor) and ((rippl\$3	DERWENT; IBM TDB	
		or corrugat\$2) near12 (plate or wall))	_	2000/00/00 11 55
_	0	<pre>((((borosilicate or boro-silicate) adj glass or bpsg or germanium adj</pre>	USPAT; US-PGPUB;	2002/02/08 14:22
,		(borosilicate or boro-silicate) adj glass or ge-bpsg) near12 (stack\$2 or	EPO; JPO; DERWENT;	
		alternat\$3)) same capacitor) and ((rippl\$3	IBM_TDB	
_	2	or corrugat\$2)) (((borosilicate or boro-silicate) adj	USPAT;	2002/02/08 15:32
		glass or bpsg or germanium adj (borosilicate or boro-silicate) adj glass	US-PGPUB; EPO; JPO;	
		or ge-bpsg) near12 capacitor) and	DERWENT;	
_	0	<pre>((rippl\$3 or corrugat\$2) near12 capacitor) ((germanium adj (borosilicate or</pre>	IBM_TDB USPAT;	2002/02/08 15:35
		boro-silicate) adj glass or ge-bpsg)	US-PGPUB;	
		near12 (borosilicate or boro-silicate) adj glass) near12 (capacitance or capacitor or	EPO; JPO; DERWENT;	
		stacked or stacking)	IBM TDB	

-	512	((germanium adj (borosilicate or	USPAT;	2002/02/08 15:37
		boro-silicate) adj glass or ge-bpsg)	US-PGPUB;	
		near12 (borosilicate or boro-silicate) adj glass or bpsg) near12 (capacitance or	EPO; JPO; DERWENT;	
		capacitor or stacked or stacking or	IBM TDB	
		alternate or alternating or alternatingly)	15.1_155	
_	51	((germanium adj (borosilicate or	USPAT;	2002/02/08 15:37
1		boro-silicate) adj glass or ge-bpsg) with	US-PGPUB;	
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
		or bpsg) near12 (capacitance or capacitor	DERWENT;	
		or stacked or stacking or alternate or	IBM_TDB	
		alternating or alternatingly)		
-	646	((germanium adj (borosilicate or	USPAT;	2002/02/08 15:37
		boro-silicate) adj glass or ge-bpsg) with	US-PGPUB;	
		(borosilicate or boro-silicate) adj glass or bpsg) with (capacitance or capacitor or	EPO; JPO; DERWENT;	
		stacked or stacking or alternate or	IBM TDB	
		alternating or alternatingly)	156-155	i
_	51		USPAT;	2002/02/08 15:37
	-	boro-silicate) adj glass or ge-bpsg) with	US-PGPUB;	2002, 02, 00 1010.
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
1		or bpsg) near10 (capacitance or capacitor	DERWENT;	
		or stacked or stacking or alternate or	IBM_TDB	
1		alternating or alternatingly)		
-	38	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	USPAT;	2002/02/08 15:38
		boro-silicate) adj glass or ge-bpsg) with	US-PGPUB;	
		(borosilicate or boro-silicate) adj glass or bpsg) near10 (capacitance or capacitor	EPO; JPO; DERWENT;	
		or stacked or stacking or alternate or	IBM TDB	
		alternating or alternatingly) and dram	100-100	
_	30	((germanium adj (borosilicate or	USPAT	2002/02/08 15:46
		boro-silicate) adj glass or ge-bpsg) with		,,
1		(borosilicate or boro-silicate) adj glass		
		or bpsg) near10 (capacitance or capacitor		
		or stacked or stacking or alternate or		
	_	alternating or alternatingly) and dram		
-	0	1,5	USPAT	2002/02/08 15:40
		boro-silicate) adj glass or ge-bpsg) with		
		(borosilicate or boro-silicate) adj glass or bpsg) near10 (capacitance or capacitor		
		or stacked or stacking or alternate or		
		alternating or alternatingly) and dram and		
		corrugat\$3		
-	0	((germanium adj (borosilicate or	USPAT;	2002/02/08 15:40
		boro-silicate) adj glass or ge-bpsg) with	US-PGPUB;	
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
		or bpsg) near10 (capacitance or capacitor	DERWENT;	
		or stacked or stacking or alternate or	IBM_TDB	
		alternating or alternatingly) and dram and corrugat\$3		
_	0	((germanium adj (borosilicate or	USPAT;	2002/02/08 15:41
		boro-silicate) adj glass or ge-bpsg) with	US-PGPUB;	2002/02/00 13.41
		(borosilicate or boro-silicate) adj glass	EPO; JPO;	
		or bpsg) near10 (capacitance or capacitor	DERWENT;	
		or stacked or stacking or alternate or	IBM_TDB	
		alternating or alternatingly) and dram and	_ ·	
	_ ا	(rippl\$3 or corrugat\$3)		
-	0	((germanium adj (borosilicate or	USPAT;	2002/02/08 15:42
		boro-silicate or boro-silicate add glass	US-PGPUB;	
		(borosilicate or boro-silicate) adj glass or bpsg) near10 (capacitance or capacitor	EPO; JPO; DERWENT;	
		or stacked or stacking or alternate or	IBM TDB	
		alternating or alternatingly) and dram and	12.1_122	
		(rippl\$3 or corrugat\$3 or standing adj		
		wav\$3)		
-	30	(ge-bpsg and (borosilicate or	USPAT	2002/02/08 15:47
		boro-silicate) adj glass or bpsg) near10		
		(capacitance or capacitor or stacked or		
		stacking or alternate or alternating or		
		alternatingly) and dram		

,				
-	0	(ge-bpsg and (borosilicate or	USPAT	2002/02/08 15:48
	1	boro-silicate) adj glass or bpsg) near10]
	-	(capacitance or capacitor or stacked or		
		stacking or alternate or alternating or		
		alternatingly) and (rippl\$3 or corrugat\$3)		-
		and dram	HODAM	2002/02/02 15:40
-	0	1 (3	USPAT	2002/02/08 15:49
		boro-silicate) adj glass or bpsg) near10		
		(capacitance or capacitor or stacked or		
		stacking or alternate or alternating or		
	0	alternatingly) and (rippl\$3 or corrugat\$3)	HCDAM	2002/02/08 15:50
_		(3: -F-2 (F	USPAT	2002/02/08 15:50
İ		or stacked or stacking or alternate or		
		alternating or alternatingly)) and (rippl\$3 or corrugat\$3)		
1_	0	(ge-bpsg or germanium-boro-phospho adj	USPAT	2002/02/08 15:56
		silicate adj glass or germanium adj	USERI	2002/02/08 13:30
		boro-phospho adj silicate adj glass or		
		germanium-boro-phospho-silicate adj glass		
		or germanium adj boro adj phospho adj		
	[silicate adj glass) same (stacked or		
	[stacking or alternating or alternate or	ļ	
		alternately or multi-layer or multi adj	1	
	1	layer or laminat\$3)		
_	2	ge-bpsg or germanium-boro-phospho adj	USPAT	2002/02/08 15:56
		silicate adj glass or germanium adj	55171	2002/02/00 13.30
		boro-phospho adj silicate adj glass or		
		germanium-boro-phospho-silicate adj glass		
		or germanium adj boro adj phospho adj		
		silicate adj glass or ge-bpsg		i
-	1	5648175.pn.	USPAT	2002/02/09 10:09
_	14	(("5061650") or ("5240871") or ("5300801")	USPAT	2002/02/09 10:14
		or ("5466627") or ("5637523") or		=====================================
		("5656536") or ("5827783") or ("5843822")		
		or ("5879987") or ("6025225") or		
		("6027970") or ("6028763") or ("6060355")		
		or ("6074926")).PN.		
_	0	((("5061650") or ("5240871") or	USPAT;	2002/02/09 10:14
		("5300801") or ("5466627") or ("5637523")	US-PGPUB;	
		or ("5656536") or ("5827783") or	EPO; JPO;	
		("5843822") or ("5879987") or ("6025225")	DERWENT;	
		or ("6027970") or ("6028763") or	IBM_TDB	
		("6060355") or ("6074926")).PN.) and	_	
1		corrugat\$3 and capacit\$3 and bpsg and		
		ge-bpsg		
-	0	((("5061650") or ("5240871") or	USPAT;	2002/02/09 10:14
		("5300801") or ("5466627") or ("5637523")	US-PGPUB;	
		or ("5656536") or ("5827783") or	EPO; JPO;	
		("5843822") or ("5879987") or ("6025225")	DERWENT;	
		or ("6027970") or ("6028763") or	IBM_TDB	
.		("6060355") or ("6074926")).PN.) and		
		capacit\$3 and bpsg and ge-bpsg		
-	118	((increase near5 capacitance) near5	USPAT;	2002/02/09 10:18
		surface) near5 (rough\$5 or etch\$3)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
-	0		USPAT;	2002/02/09 10:17
		surface) near5 (rough\$5 or etch\$3) and	US-PGPUB;	
] .		"L14"	EPO; JPO;	
			DERWENT;	
	ا ء		IBM_TDB	
-	0	((increase near5 capacitance) near5	USPAT;	2002/02/09 10:17
		surface) near5 (rough\$5 or etch\$3) and	US-PGPUB;	
		"L14"	EPO; JPO;	
			DERWENT;	
L			IBM TDB	

-	131	((("5061650") or ("5240871") or	USPAT;	2002/02/09 10:18
		("5300801") or ("5466627") or ("5637523")	US-PGPUB;	
		or ("5656536") or ("5827783") or	EPO; JPO;	
		("5843822") or ("5879987") or ("6025225")	DERWENT;	_
		or ("6027970") or ("6028763") or	IBM_TDB	
1		("6060355") or ("6074926")).PN.) or		
		(((increase near5 capacitance) near5		
		surface) near5 (rough\$5 or etch\$3))		
-	35		USPAT;	2002/02/09 10:21
		("5300801") or ("5466627") or ("5637523")	US-PGPUB;	
		or ("5656536") or ("5827783") or	EPO; JPO;	
[("5843822") or ("5879987") or ("6025225")	DERWENT;	
}		or ("6027970") or ("6028763") or	IBM_TDB	
		("6060355") or ("6074926")).PN.) or		İ
		(((increase near5 capacitance) near5		
	1	surface) near5 (rough\$5 or etch\$3))) and		
		((increas\$3 near5 capacitance) near5		
		etch\$3)		
-	6		USPAT;	2002/02/09 10:41
]	("5300801") or ("5466627") or ("5637523")	US-PGPUB;	
		or ("5656536") or ("5827783") or	EPO; JPO;	1
		("5843822") or ("5879987") or ("6025225")	DERWENT;	
		or ("6027970") or ("6028763") or	IBM_TDB	
] .		("6060355") or ("6074926")).PN.) or	-	
		(((increase near5 capacitance) near5		
		surface) near5 (rough\$5 or etch\$3))) and		
		((increas\$3 near5 capacitance) near5		
		etch\$3)) and bpsg		
-	2	(((((("5061650") or ("5240871") or	USPAT;	2002/02/09 10:42
		("5300801") or ("5466627") or ("5637523")	US-PGPUB;	
		or ("5656536") or ("5827783") or	EPO; JPO;	
		("5843822") or ("5879987") or ("6025225")	DERWENT;	
		or ("6027970") or ("6028763") or	IBM TDB	
1		("6060355") or ("6074926")).PN.) or	_	
		(((increase near5 capacitance) near5		
		surface) near5 (rough\$5 or etch\$3))) and		
		((increas\$3 near5 capacitance) near5		
		etch\$3)) and bpsg) and germanium		
-	166	different adj etch\$3 adj2 rates and bpsg	USPAT;	2002/02/09 10:42
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	0		USPAT;	2002/02/09 10:43
		bpsg) near5 capacitance	US-PGPUB;	į
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	11	different adj etch\$3 adj2 rates near5 bpsg	USPĀT;	2002/02/09 11:09
			US-PGPUB;	
		·	EPO; JPO;	
			DERWENT;	[
			IBM_TDB	
-	507	etch\$3 adj rate same bpsg	USPAT;	2002/02/09 11:09
1			US-PGPUB;	
1			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
-	318	etch\$3 adj rate with bpsg	USPAT;	2002/02/09 11:09
]	• •	US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1	etch\$3 adj rate with (bpsg and (ge-bpsg or	USPĀT;	2002/02/09 16:42
]		germanium))	US-PGPUB;	
1]		EPO; JPO;	
	}		DERWENT;	
1	1		IBM TDB	

		· · · · · · · · · · · · · · · · · · ·	· · · · · · · · · · · · · · · · · · ·	· · · · · · · · · · · · · · · · · · ·
-	3	5827783.pn.	USPAT; US-PGPUB;	2002/02/09 17:35
			EPO; JPO;	
]		DERWENT;	
			IBM_TDB	
-	68	(USPAT;	2002/02/09 17:36
		memory adj device.ti,ab.	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	25		USPAT;	2002/02/09 17:55
		memory adj device.ti,ab.	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	((si-ge or silicon-germanium) same	USPAT;	2002/02/09 22:09
		capacitor same dielectric) and memory adj device.ti,ab.	US-PGPUB; EPO; JPO;	
		device. ci, ab.	DERWENT;	
			IBM TDB	
-	2	5930106.pn.	USPAT;	2002/02/09 18:01
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	4791		USPĀT;	2004/07/23 20:03
1		(257/296) or (257/298) or (257/300) or	US-PGPUB;	
		(257/303) or (257/306) or (257/516) or (257/532) or (257/906)).CCLS.	EPO; JPO; DERWENT;	
		(237, 332, 31 (237, 330), 13023.	IBM TDB	
-	3		USPĀT;	2002/02/09 22:11
		or ("257/296") or ("257/298") or	US-PGPUB;	
		("257/300") or ("257/303") or ("257/306") or ("257/516") or ("257/532") or	EPO; JPO; DERWENT;	
İ		("257/906")).CCLS.) and bpsg and germanium	IBM TDB	
		and capacitor and memory adj2		
	3	device.ti,ab.		0000/00/00 00 10
-	3	5827783.pn.	USPAT; US-PGPUB;	2002/02/09 22:12
			EPO; JPO;	
			DERWENT;	
_	3	5804506.pn.	IBM_TDB	2002/02/00 22-12
	3	3604306.pm.	USPAT; US-PGPUB;	2002/02/09 22:13
			EPO; JPO;	
			DERWENT;	
_	3	5889696.pn.	IBM_TDB USPAT;	2002/02/09 22:13
	١	, 0005050.pir.	US-PGPUB;	2002/02/03 22:13
			EPO; JPO;	
			DERWENT;	
_	2	5889696.pn.	<pre>IBM_TDB USPAT;</pre>	2002/02/10 09:09
	_	- 0005050.pii.	DERWENT	2002/02/10 09:09
-	2	5930106.pn.	USPAT;	2002/02/10 09:10
_		(323/530) CCLC	DERWENT	2000/05/00 55 55
-	0	(323/539).CCLS.	USPAT; US-PGPUB;	2002/05/08 16:56
			EPO; JPO;	
			DERWENT;	
_	1364	(band adj gap or bandgap) adj reference	IBM_TDB	2002/05/00 16:57
	1304	near5 voltage	USPAT; US-PGPUB;	2002/05/08 16:57
			EPO; JPO;	
	!		DERWENT;	
_	275	(handgan) add reference nears well-account	IBM TDB	2002/05/00 16:50
	213	(bandgap) adj reference near5 voltage and bipolar adj transistor	USPĀT; US-PGPUB;	2002/05/08 16:58
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	155	(327/539).CCLS.	USPAT;	2002/05/08 16:58
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	2	("5804506").PN.	USPAT;	2002/12/05 11:50
	_	(3001300) 12111	US-PGPUB;	2002/12/03 11:30
			EPO; JPO;	1
			DERWENT;	
			IBM_TDB	
-	2	("5972769").PN.	USPAT;	2002/12/05 10:56
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	2	("6376303").PN.	USPAT;	2002/12/05 10:57
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	l i
	2	(#5007700#) 72	IBM_TDB	0000/10/05 10 11
-	2	("5827783").PN.	USPAT;	2002/12/05 13:11
	1		US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	5502		USPAT;	2004/07/23 18:11
		(257/296) or (257/298) or (257/300) or	US-PGPUB;	
		(257/303) or (257/306) or (257/516) or	EPO; JPO;	
		(257/532) or (257/906)).CCLS.	DERWENT;	
_	13	(((257/68) or (257/71) or (257/277) or	IBM_TDB USPAT;	2002/12/05 12:12
	13	((257/296) or (257/298) or (257/300) or	US-PGPUB;	2002/12/05 13:13
		(257/303) or (257/306) or (257/516) or	EPO; JPO;	
		(257/532) or (257/906)).CCLS.) and	DERWENT;	
		corrugat\$3 near15 (capacitor or	IBM TDB	
	_	capacitance) and memory.ti,ab.	_	
-	3	, ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	USPAT;	2003/05/27 13:16
		side adj wall)) and stacked adj capacitor and germanium and (BPSG	US-PGPUB;	-
		boro-phosphosilicate adj glass)	EPO; JPO; DERWENT;	
		boto phosphostiteace day grass/	IBM TDB	
-	381	(boro-phosphosilicate adj glass BPSG boro	USPAT;	2003/05/27 13:17
		adj phospho-silicate adj glass) and	US-PGPUB;	
		germanium and capacitor	EPO; JPO;	
			DERWENT;	
_	3	(boro-phosphosilicate adj glass BPSG boro	IBM_TDB USPAT;	2003/05/27 13:18
		adj phospho-silicate adj glass) and	US-PGPUB;	2003/03/21 13:18
		germanium and capacitor and (corrugated	EPO; JPO;	
		corrugation)	DERWENT;	
1		<u> </u>	IBM_TDB	
-	109	(boro-phosphosilicate adj glass BPSG boro	USPAT;	2003/05/27 13:19
		adj phospho-silicate adj glass) and germanium and stacked adj capacitor	US-PGPUB;	
		germanium and stacked adj capacitor	EPO; JPO; DERWENT;	
]			IBM TDB	
-	22	(boro-phosphosilicate adj glass BPSG boro	USPAT;	2003/05/27 13:22
		adj phospho-silicate adj glass) and	US-PGPUB;	
[germanium and stacked adj	EPO; JPO;	
		capacitor.ti,ab,clm.	DERWENT;	
_	0	("6651946").PN.	IBM_TDB USPAT;	2003/05/27 12:00
		(COOLDIO).IN.	US-PGPUB;	2003/05/27 13:22
			EPO; JPO;	
	[DERWENT;	
			IBM TDB	
-	2	("6346455").PN.	USPAT;	2003/05/27 13:23
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	1	"6074926".PN.	USPAT	2003/05/27 13:23
<u> </u>			001111	_2000/00/2/ 10.20

		HCOCOSEER DV	LIGDAM	1 2002 (05 (27 12:24
	1 30	"6060355".PN. (US-5874756-\$ or US-6008515-\$ or US-4716548-\$ or US-5545585-\$ or US-6124607-\$ or US-6190992-\$ or US-6303430-\$ or US-5889696-\$ or US-5930106-\$ or US-6376303-\$ or US-5804506-\$ or US-5648175-\$ or US-6656536-\$ or US-5648175-\$ or US-6087694-\$ or US-6150208-\$ or US-4894696-\$ or US-5250458-\$ or US-5519238-\$ or US-5233992-\$ or US-5438011-\$ or US-4855953-\$ or US-4845539-\$ or US-5471087-\$ or US-5835337-\$ or US-5972769-\$).did. or (US-4786954-\$).did. or	USPAT; USPAT; US-PGPUB; EPO; DERWENT	2003/05/27 13:24 2003/05/27 13:29
	1	(US-20010006449-\$).did. or (EP-507683-\$).did. or (US-5889696-\$).did. ((US-5874756-\$ or US-6008515-\$ or US-4716548-\$ or US-5545585-\$ or US-6124607-\$ or US-6190992-\$ or US-6303430-\$ or US-5889696-\$ or US-5930106-\$ or US-6376303-\$ or US-5804506-\$ or US-6159792-\$ or US-5656536-\$ or US-5648175-\$ or US-6087694-\$ or US-6150208-\$ or US-519238-\$ or US-5250458-\$ or US-5438011-\$ or US-4855953-\$ or US-5438011-\$ or US-5471087-\$ or US-5835337-\$ or US-5972769-\$).did. or (US-4786954-\$).did. or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 13:39
-	2	(US-20010006449-\$).did. or (EP-507683-\$).did. or (US-5889696-\$).did.) and haller.in. ("6346455").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/27 14:15
-	4	BPSG near2 layer and Ge-BPSG near2 layer and semiconductor.ti,ab,clm. and memory.ti,ab,clm.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/27 14:20
-	4	BPSG near2 layer and Ge-BPSG near2 layer and semiconductor.ti,ab,clm.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/27 14:21
-	1	(boro-phospho-silicate boro-phosphosilicate boro adj phosphosilicate BPSG) near2 layer and (germanium-doped near4 (boro-phospho-silicate BPSG Ge-BPSG) near4	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 14:48
-	664	layer) (PSG phosphorus near2 doped adj glass) and germanium and (BPSG boron PBSG)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/27 14:50
_	280	(PSG phosphorus near2 doped adj glass) and germanium and (BPSG boron PBSG) and capacitor	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/27 14:56
_	114	(PSG phosphorus near2 doped adj glass) and germanium and (BPSG boron PBSG) and capacitor.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/27 15:02

			T	1
-	16	1 3	USPAT;	2003/05/27 15:09
İ		boro\$1phoshosilicate) and	US-PGPUB;	
ļ		capacitor.ti,ab,clm.	EPO; JPO;	
			DERWENT;	ĺ
			IBM TDB	
_	14	(("5061650") or ("5240871") or ("5300801")	USPAT	2003/05/27 15:21
		or ("5466627") or ("5637523") or		İ
		("5656536") or ("5827783") or ("5843822")		
		or ("5879987") or ("6025225") or		<u> </u>
		("6027970") or ("6028763") or ("6060355")		
	Į	or ("6074926")).PN.		
_	0		USPAT;	2003/05/27 15:23
-	"	corrugated) and capacitor").PN.	US-PGPUB;	2003/03/27 13.23
		corrugated) and capacitor).FN.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/05/05 15 10
-	40	· · · · · · · · · · · · · · · ·	USPAT;	2003/05/27 15:48
		corrugated) and capacitor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	21		USPAT;	2003/05/27 15:48
		corrugated) and capacitor) and ("1:4"	US-PGPUB;	
		"4:1")	EPO; JPO;	
1	1		DERWENT;	
1			IBM TDB	
l _	2	("5827783").PN.	USPAT;	2003/09/27 20:00
	-	\ 3021703 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	US-PGPUB;	2003/03/27 20:00
			EPO; JPO;	
			DERWENT;	
		#6007F00#	IBM_TDB	0000/11/10 11 50
-		"5827783"	USPAT	2003/11/13 14:59
-	1	("5827783").PN.	USPAT	2003/11/13 15:00
-	1	("5804506").PN.	USPAT	2003/11/13 15:00
-	2	("5827783").PN.	USPAT;	2003/11/16 19:41
		·	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	2	("5804506").PN.	USPAT;	2003/11/16 19:41
			US-PGPUB;	ĺ
	İ		EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	6351	((257/68) or (257/71) or (257/277) or	USPĀT;	2003/11/16 20:23
		(257/296) or (257/298) or (257/300) or	US-PGPUB;	
		(257/303) or (257/306) or (257/516) or	EPO; JPO;	
]	(257/532) or (257/906)).CCLS.	DERWENT;	
		, , , , , , , , , , , , , , , , , , ,	IBM TDB	
_	20	(((257/68) or (257/71) or (257/277) or	USPAT;	2003/11/16 20:49
		(257/296) or (257/298) or (257/300) or	US-PGPUB;	=====================================
		(257/303) or (257/306) or (257/516) or	EPO; JPO;	
1		(257/532) or (257/906)).CCLS.) and	DERWENT;	
		(corrugated corrugation) near12 capacitor		
			IBM_TDB	
		and (capacitor adj cell dram adj cell		
		memory adj cell semiconductor near2		
	_	(device element)).ti,ab,clm.	TIGDAM:	2002/11/16 22 55
-	5		USPAT;	2003/11/16 20:57
		phospho-silicate BSG BFSG BSG:F boro adj	US-PGPUB;	
		phospho adj silicate boro adj phospho adj	EPO; JPO;	
		silicate) and (corrugated corrugation)	DERWENT;	
		near12 capacitor and (capacitor adj cell	IBM_TDB	
		dram adj cell memory adj cell		
		semiconductor near2 (device		
		element)).ti,ab,clm.		

-	5	(boro-phospho-silicate boro adj	USPAT;	2003/11/16 20:58
		phospho-silicate BSG BFSG BSG:F boro adj	US-PGPUB;	
		phospho adj silicate boro adj phospho adj	EPO; JPO;	
		silicate) and (corrugated-trench adj	DERWENT;	
		capacitor ccc adj structure (corrugated corrugation) near12 capacitor) and	IBM_TDB	
		(capacitor adj cell dram adj cell memory		1
		adj cell semiconductor near2 (device		
		element)).ti,ab,clm.		
_	7		USPAT;	2003/11/17 08:28
		(bpsg boro adj phospho adj silicate)	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	10	(corrugated-trench adj capacitor ccc adj	USPAT;	2003/11/17 08:33
		structure (corrugated corrugation) near12	US-PGPUB;	
-	,	capacitor) and wall and (bpsg boro adj	EPO; JPO;	1
		phospho adj silicate)	DERWENT	
-	4	,	USPAT;	2003/11/17 08:41
		structure (corrugated corrugation) near12	US-PGPUB;	
		capacitor) and wall near12 (bpsg boro adj	EPO; JPO;	
1_	8	phospho adj silicate) (BPSG boro adj phospho adj silicate)	DERWENT	2003/11/17 08:56
-		near12 wall near12 capacitor	USPAT; US-PGPUB;	2003/11/1/ 08:56
		Heariz warr Heariz Capacitor	EPO; JPO;	
			DERWENT	
_	8	(BPSG boro adj phospho adj silicate)	USPAT;	2003/11/17 08:57
	I	near12 wall near12 capacitor and	US-PGPUB;	
		(insulating dielectric)	EPO; JPO;	
		, ,,	DERWENT	
_	6351	((257/68) or (257/71) or (257/277) or	USPAT;	2003/11/17 10:12
		(257/296) or (257/298) or (257/300) or	US-PGPUB;	
		(257/303) or (257/306) or (257/516) or	EPO; JPO;	
		(257/532) or (257/906)).CCLS.	DERWENT;	
			IBM_TDB	
-	3	(((257/68) or (257/71) or (257/277) or	USPAT;	2003/11/17 10:12
		(257/296) or (257/298) or (257/300) or	US-PGPUB;	
	[(257/303) or (257/306) or (257/516) or	EPO; JPO;	
		(257/532) or (257/906)).CCLS.) and	DERWENT;	
		corrugated near6 capacitor and (boro adj phospho adj silicate BPSG)	IBM_TDB	
_	2	("5827783").PN.	USPAT;	2004/05/03 13:57
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	2	("6097053").PN.	USPAT;	2004/05/03 13:58
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		(11500450511) 727	IBM_TDB	0004/05/05
-	2	("5804506").PN.	USPAT;	2004/05/04 15:24
			US-PGPUB;	
1	[EPO; JPO;	
			DERWENT; IBM TDB	
_	7	(("5519238") or ("5623243") or	USPAT;	2004/05/03 14:31
	 	("5830793")).PN.	US-PGPUB;	2004/00/00 14.01
			EPO; JPO;	
			DERWENT;	
-			IBM TDB	
-	5	(bpsg near3 (germanium ge) ge-bpsg) and	USPAT;	2004/05/04 10:00
		capacitor and (corrugate corrugated	US-PGPUB;	
		corrugating corrugation corrugates)	EPO; JPO;	
]			DERWENT;	
	_		IBM_TDB	
-	5	(bpsg near3 (germanium ge) ge-bpsg) and	USPAT;	2004/05/04 10:02
		capacitor and (corrugate corrugated	US-PGPUB;	[
		corrugating corrugation corrugates ripple	EPO; JPO;	· i
		rippled ripples rippling)	DERWENT;	
<u> </u>			IBM TDB	

_	25	(bpsg near3 (germanium ge) ge-bpsg) and	USPAT;	2004/05/04 10:02
		capacitor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/05/04 10:35
-	20	((bpsg near3 (germanium ge) ge-bpsg) and	USPAT;	2004/05/04 10:35
		capacitor) not ((bpsg near3 (germanium ge)	US-PGPUB;	
		ge-bpsg) and capacitor and (corrugate corrugated corrugating corrugation	EPO; JPO; DERWENT;	
1		corrugated corrugating corrugation corrugates ripple rippled ripples	IBM TDB	
		rippling))	1517_155	
_	21		USPAT;	2004/05/04 10:36
		and capacitor) not ((bpsg near3 (germanium	US-PGPUB;	
		ge) ge-bpsg) and capacitor and (corrugate	EPO; JPO;	
		corrugated corrugating corrugation	DERWENT;	
		corrugates ripple rippled ripples	IBM_TDB	
	_	rippling))		
-	6	((bpsg near3 (germanium ge) ge-bpsg gepsg)	USPAT;	2004/05/04 10:36
		and capacitor) not (((bpsg near3	US-PGPUB;	
	1	(germanium ge) ge-bpsg) and capacitor) not	EPO; JPO;	
	1	((bpsg near3 (germanium ge) ge-bpsg) and capacitor and (corrugate corrugated	DERWENT; IBM TDB	
		corrugating corrugation corrugates ripple	100-100	
		rippled ripples rippling)))		
-	424	257/68	USPAT;	2004/05/04 15:24
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		058/54	IBM_TDB	0004/85/53
-	398	257/71	USPAT;	2004/05/04 15:25
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	270	257/277	USPAT;	2004/05/04 15:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1116	057/006	IBM_TDB	0004/05/04 15 05
_	4446	257/296	USPAT; US-PGPUB;	2004/05/04 15:25
			EPO; JPO;	
1			DERWENT;	
}			IBM TDB	
-	877	257/298	USPAT;	2004/05/04 15:25
			US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
1_	1002	257/300	IBM_TDB USPAT;	2004/05/04 15:25
1	1002	2377300	US-PGPUB;	2004/05/04 15:25
1			EPO; JPO;	
1			DERWENT;	
1			IBM_TDB	
-	1278	257/303	USPĀT;	2004/05/04 15:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	3123	257/306	IBM_TDB USPAT;	2004/05/04 15:25
	3123	25,7500	US-PGPUB;	2004/03/04 13:23
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	280	257/516	USPĀT;	2004/05/04 15:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
L			IBM_TDB	L

		1 057 /520	I	1 0001/05/01 15 05
-	2215	257/532	USPAT;	2004/05/04 15:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	227	257/906	USPAT;	2004/05/04 15:26
	İ		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	9952	257/68 257/71 257/277 257/296 257/298	USPĀT;	2004/05/04 15:26
		257/300 257/303 257/306 257/516 257/532	US-PGPUB;	
		257/906	EPO; JPO;	
			DERWENT;	
			IBM TDB	
1_	240	(257/68 257/71 257/277 257/296 257/298	USPAT;	2004/05/04 15:27
	240	257/300 257/303 257/306 257/516 257/532	US-PGPUB;	2004/05/04 15.27
ļ				
		257/906) and (corrugat\$3 etch\$3 near2 rate	EPO; JPO;	
1		rippl\$3) and bpsg and capacitor.ti,ab,clm.	DERWENT;	
			IBM_TDB	<i>.</i>
-	2	("4631803").PN.	USPAT;	2004/05/04 16:02
			US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
1 -	2	("5827783").PN.	USPĀT;	2004/07/23 16:33
i			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	("6097053").PN.	USPAT;	2004/07/23 16:34
	_	(0031000 / 12111	US-PGPUB;	2004/07/23 10:54
	i		EPO; JPO;	
			DERWENT;	
			IBM TDB	
	2	("5804506").PN.		0004/07/02 17 56
-	2	("3804306").PN.	USPAT;	2004/07/23 17:56
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	10270		USPAT;	2004/07/23 18:12
		257/71	US-PGPUB;	
		257/277	EPO; JPO;	
		257/296	DERWENT;	
		257/298	IBM TDB	
		257/300	_	
		257/303		
	ļ .	257/306		
1		257/516		
1		257/532		
1		257/906		
I -	ا م	(257/68	USPAT;	2004/07/23 18:17
]	257/71	· ·	2004/07/23 10:17
			US-PGPUB;	
	! !	257/277	EPO; JPO;	
1		257/296	DERWENT;	
1		257/298	IBM_TDB	
		257/300		
		257/303		
	, 1	257/306		i
		257/516		
1		257/532		
		257/906) and memory and capacitor adj cell		
		and (boro-phospho adj silicate BPS BPSG)		
		near4 (germanium Ge) and ((increase		
1		increasing increased increases) near4		
		capacitance (corrugate corrugation		i
		corrugated))		
·				

[-	4	(257/68	USPAT;	2004/07/23 18:18
		257/71	US-PGPUB;	
		257/277	EPO; JPO;]
		· ·		
		257/296	DERWENT;	
	1	257/298	IBM_TDB	
		257/300		
		257/303		
		257/306		
		257/516		
		257/532		
		257/906) and memory and capacitor adj cell		
	1	and (boro-phospho adj silicate BPS BPSG)	İ	j
		near4 (germanium Ge) and ((increase		1
		increasing increased increases) near4		
		capacitance (corrugate corrugation		
		corrugated rippled ripples rippling))		0004/07/00 10 00
-	4	(257/68	USPAT;	2004/07/23 18:33
		257/71	US-PGPUB;	
		257/277	EPO; JPO;	
		257/296	DERWENT;	
	1	257/298	IBM TDB	
		1	TOIT _ TOB	
		257/300		
		257/303		
	1	257/306		
	1	257/516]	
		257/532]	
		257/906) and memory and capacitor adj cell		
	İ		1	
	1	and (boro-phospho adj silicate BPS BPSG)		1
		near4 (germanium Ge) and ((increase	ļ	
	1	increasing increased increases) near4		1
		capacitance (corrugate corrugation		1
		corrugated rippled ripples rippling		1
1		roughen roughened roughens roughening))		
1_	0		USPAT;	2004/07/23 18:34
1	8	memory.ti,ab,clm. and capacitor adj cell	· ·	2004/01/23 18:34
		and (boro-phospho adj silicate BPS BPSG)	US-PGPUB;	
1		near4 (germanium Ge) and ((increase	EPO; JPO;	
		increasing increased increases) near4	DERWENT;	
		capacitance (corrugate corrugation	IBM TDB	
		corrugated rippled ripples rippling	_	
		roughen roughened roughens roughening))		
			tionam.	2004/07/22 10:46
-	5	(memory.ti,ab,clm. and capacitor adj cell	USPAT;	2004/07/23 18:46
		and (boro-phospho adj silicate BPS BPSG)	US-PGPUB;	
		near4 (germanium Ge) and ((increase	EPO; JPO;	
		increasing increased increases) near4	DERWENT;	
1	1	capacitance (corrugate corrugation	IBM TDB	
1	1	corrugated rippled ripples rippling		
	1			
	1	roughen roughened roughens roughening)))		
	1	not ((257/68		
	1	257/71		
		257/277		
	1	257/296		
		257/298		
1		257/300		
		257/303		
		257/306		
		257/516		
		257/532		
		257/906) and memory and capacitor adj cell		
		and (boro-phospho adj silicate BPS BPSG)		
				<u> </u>
		near4 (germanium Ge) and ((increase		
		increasing increased increases) near4		
		capacitance (corrugate corrugation		
		corrugated rippled ripples rippling		
		roughen roughened roughens roughening)))		
_	1	"5061650".PN.	USPAT	2004/07/23 18:36
l _	1	"5240871".PN.		
-	1		USPAT	2004/07/23 18:37
_	1	"5300801".PN.	USPAT	2004/07/23 18:37
-	1	"5466627".PN.	USPAT	2004/07/23 18:37
-	1	"5637523".PN.	USPAT	2004/07/23 18:37
-	1	"5656536".PN.	USPAT	2004/07/23 18:38
_	ī	"5827783".PN.	USPAT	2004/07/23 18:39
_	1	"5843822".PN.	USPAT	2004/07/23 18:39
		JU33022 .FN.	OSEMI	L 2004/01/23 TQ:39

				1
-	1	"5879987".PN.	USPAT	2004/07/23 18:39
-	1	"6025225".PN.	USPAT	2004/07/23 18:39
-	1	"6027970".PN.	USPAT.	2004/07/23 18:39
-	1	"6028763".PN.	USPAT	2004/07/23 18:40
-	1	"6060355".PN.	USPAT	2004/07/23 18:40
-	1	"6028763".PN.	USPAT	2004/07/23 18:40
_	1	"6060355".PN.	USPAT	2004/07/23 18:41
1_	ī	"6060355".PN.	USPAT	2004/07/23 18:41
1_	1	"6060355".PN.	USPAT	2004/07/23 18:42
		"6074926".PN.	l .	2004/07/23 18:42
- '	1		USPAT	•
-	8	······	USPAT;	2004/07/23 18:46
}		and ((boro-phospho adj silicate BPS BPSG)	US-PGPUB;	
		near4 (germanium Ge))	EPO; JPO;	
			DERWENT;	
	:		IBM_TDB	
-	16	(("5061650") or ("5240871") or ("5300801")	USPAT	2004/07/23 19:22
		or ("5466627") or ("5637523") or		
		("5656536") or ("5827783") or ("5843822")		
		or ("5879987") or ("6025225") or		
		("6027970") or ("6028763") or ("6060355")		•
		or ("5804506") or ("5972769") or		
1		("6376303")).PN.		
1_	16	1 '	HCDAT	2004/07/23 19:27
-	1 10	US-5827783-\$ or US-5843822-\$ or	USPAT	2004/07/23 19:27
		US-5879987-\$ or US-6025225-\$ or		
		US-6027970-\$ or US-6028763-\$ or		
		US-5061650-\$ or US-5240871-\$ or		
		US-5300801-\$ or US-5466627-\$ or		
		US-5637523-\$ or US-5804506-\$ or		
		US-5972769-\$ or US-6376303-\$).did.		ł
-	9	((US-5656536-\$ or US-6060355-\$ or	USPAT	2004/07/23 19:30
		US-5827783-\$ or US-5843822-\$ or		
		US-5879987-\$ or US-6025225-\$ or		
		US-6027970-\$ or US-6028763-\$ or		
		US-5061650-\$ or US-5240871-\$ or		
		US-5300801-\$ or US-5466627-\$ or		
		·		
İ		US-5637523-\$ or US-5804506-\$ or		
		US-5972769-\$ or US-6376303-\$).did.) and		
İ		(bpsg ge\$bpsg)		
-	8		USPAT	2004/07/23 19:46
		US-5827783-\$ or US-5843822-\$ or		
		US-5879987-\$ or US-6025225-\$ or	•	
		US-6027970-\$ or US-6028763-\$ or		
		US-5061650-\$ or US-5240871-\$ or		
		US-5300801-\$ or US-5466627-\$ or		
		US-5637523-\$ or US-5804506-\$ or		1
· !		US-5972769-\$ or US-6376303-\$).did.) and		
		(bpsg ge\$bpsg) and capacitor		
_	7	(("5519238") or ("5623243") or	USPAT;	2004/07/23 19:46
	·	("5830793")).PN.	US-PGPUB;	
			EPO; JPO;	
]			DERWENT;	
			IBM TDB	
_	2001	thalum in haller in	_	2004/02/22 10:50
-	2891	thakur.in. haller.in.	USPAT;	2004/07/23 19:56
			US-PGPUB;	
			EPO; JPO;	İ
			DERWENT;	
			IBM_TDB	
-	9	thakur.in. and haller.in.	USPAT;	2004/07/23 19:58
1			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	"micron technologies" and (boro-phospho	USPAT;	2004/07/23 19:59
		adj silicate BPSG).clm. and capacitor.clm.	US-PGPUB;	2004/0//20 10:09
	1	and memory.clm. and (germanium Ge-BPSG)	EPO; JPO;	
		and momory.cim. and (germanium de-brod)		l i
į l			DERWENT;	
L	L,		IBM TDB	

_	9	(haller.in. thakur.in. "micron	USPAT;	2004/07/23 20:00
		technologies" micron.as.) and	US-PGPUB;	
		(boro-phospho adj silicate BPSG).clm. and capacitor.clm. and memory.clm. and	EPO; JPO; DERWENT;	
		(germanium Ge-BPSG)	IBM TDB	
l _	2424	((257/701) or (257/700)).CCLS.	USPĀT;	2004/07/23 20:06
	2.2.	((2377701) 01 (2377100)7.0023.	US-PGPUB;	2001,01,25 20100
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	(((257/701) or (257/700)).CCLS.) and (bpsg	USPAT;	2004/07/23 20:07
		boro-phospho adj silictae adj glass) near3	US-PGPUB;	}
		(germanium ge) and memory and capacitor	EPO; JPO;	
		and (etch etching)	DERWENT;	
l <u></u>	1	(((257/701) or (257/700)).CCLS.) and (bpsg	IBM_TDB USPAT;	2004/07/23 20:08
	1	boro-phospho adj silictae adj glass) near3	US-PGPUB;	2004/07/23 20:08
		(germanium ge) and memory and capacitor	EPO; JPO;	
•		and (etch etching) near4 (corrugated	DERWENT;	
		corrugation corrugate roughen roughening	IBM TDB	
		rippled ripple rippling ripples)	_	
-	1		USPAT;	2004/07/23 20:19
		boro-phospho adj silictae adj glass) near3	US-PGPUB;	
		(germanium ge) and capacitor and (etch	EPO; JPO;	
		etching) near4 (corrugated corrugation	DERWENT;	
		corrugate roughen roughening rippled	IBM_TDB	
_	625	ripple rippling ripples) (257/309).CCLS.	HCDATT.	2004/07/23 20:19
_	623	(257/309).CCLS.	USPAT; US-PGPUB;	2004/07/23 20:19
İ			EPO; JPO;	
			DERWENT;	
			IBM TDB	ĺ
_	0	((257/309).CCLS.) and (corrugat\$5	USPAT;	2004/07/23 20:20
		roughen\$3) near4 (etch\$3 and rate) and	US-PGPUB;	
		(bpsg boro adj phospho adj silicate) and	EPO; JPO;	
		(germanium ge)	DERWENT;	
			IBM_TDB	
-	2	((257/309).CCLS.) and (corrugat\$5	USPAT;	2004/07/23 20:45
		roughen\$3) near4 (etch\$3 and rate)	US-PGPUB;	
İ			EPO; JPO; DERWENT;	
			IBM TDB	
_	257	(257/534).CCLS.	USPAT;	2004/07/23 20:47
		,,,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	39	((257/534).CCLS.) and (bpsg boro adj	USPAT;	2004/07/23 20:49
		phospho adj silicate adj glass)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
<u>-</u> .	0	((257/534).CCLS.) and (bpsg boro adj	IBM_TDB USPAT;	2004/07/23 20:49
		phospho adj silicate adj glass) near10	US-PGPUB;	2004/01/23 20:49
		(germanium ge)	EPO; JPO;	
		, , , ,	DERWENT;	
			IBM TDB	
-	2	921423.ap.	USPĀT;	2004/07/25 19:01
İ			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		020742 an	IBM_TDB	2004/07/25 12 1
-	3	838743.ap.	USPAT;	2004/07/25 19:16
			US-PGPUB;	
]		EPO; JPO; DERWENT;	
			IBM TDB	
_	6	(("6051850") or ("20030160281") or	USPAT;	2004/07/25 19:22
		("6204717")).PN.	US-PGPUB;	
		•	EPO; JPO;	
			DERWENT;	
			IBM TDB	